Philips Components-Signetics

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Memory Produ	cts

82S185A 8K-bit TTL bipolar PROM

DESCRIPTION

The 82S185A is field programmable, which means that custom patterns are immediately available by following the Signetics Generic I fusing procedure. The devices are supplied with all outputs at logical Low. Outputs are programmed to a logic High level at any specified address by fusing the Ni-Cr link matrix.

This device includes on-chip decoding and one Chip Enable input for memory expansion. It features 3-State outputs for optimization of word expansion in bused organizations.

Ordering information can be found on the following page.

The 82S185A device is also processed to military requirements for operation over the military temperature range. For specifications and ordering information consult the Signetics Military Data Handbook.

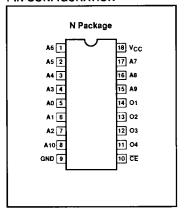
FEATURES

- Low power dissipation: 70μW/bit typ
- Address access time: 50ns max
- Input loading: -100µA max
- On-chip address decoding
- · No separate fusing pins
- Unprogrammed outputs are Low level
- Fully TTL compatible
- One Chip Enable input
- Outputs: 3-State

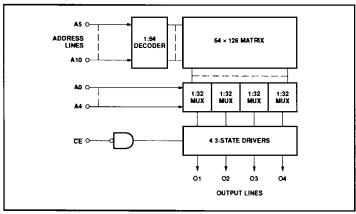
APPLICATIONS

- Microprogramming
- Control store
- Random logic
- Code conversion

PIN CONFIGURATION



BLOCK DIAGRAM



8K-bit TTL bipolar PROM (2048 × 4)

82S185A

ORDERING INFORMATION

DESCRIPTION ORDER CODE	
18-Pin Plastic Dual-In-Line 300mil-wide	N82S185A N

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
Vcc	Supply voltage	+7.0	V _{DC}
V _{IN}	input voltage	+5.5	V _{DC}
Vo	Output voltage Off-State	+5.5	V _{DC}
T _{amb}	Operating temperature range	0 to +75	°C
T _{stg}	Storage temperature range	-65 to +150	

DC ELECTRICAL CHARACTERISTICS

 $0^{\circ}C \le T_{amb} \le +75^{\circ}C, 4.75V \le V_{CC} \le 5.25V$

				LIMITS		
SYMBOL PARAMETER		TEST CONDITIONS ^{1,2}	Min	Typ ³	Max	UNIT
Input voit	age					
V _{IL}	Low	V _{CC} = 4.75V	V _{CC} = 4.75V 0.8			
V _{IH}	High	V _{CC} = 5.25V	2.0	1		V
V _{IC}	Clamp	I _{IN} = -12mA		-0.8	-1.2	٧
Output vo	Itage					
		CE = Low				_
Vol	Low	l _{OUT} ≃ 16mA			0.45	٧
V _{OH}	High	l _{OUT,} = -2mA	2.4			٧
Input curi	ent					
I _{IL}	Low	V _{IN} = 0.45V			-100	μΑ
I _{IH}	High	V _{IN} = 5.5V		İ	40	μA
Output cu	rrent					
loz	Hi-Z state	CE = High, V _{OUT} = 0.5V	0.5V -40		-40	μА
		\overline{CE} = High, V_{OUT} = 5.5V	- 1		40	μΑ
los	Short circuit ⁴	\overline{CE} = Low, V_{OUT} = 0V, High stored	-15		-70	mA
Supply cu	errent ⁵		•			
lcc		V _{CC} = 5.25V		110	155	mA
Capacitar	ice		-	•		
		CE = High, V _{CC} = 5.0V		f		
CIN	Input	$V_{IN} = 2.0V$		5		pF
Cout	Output	V _{OUT} = 2.0V		8		pF

- 1. Positive current is defined as into the terminal referenced.

- All voltages with respect to network ground.
 All typical values are at V_{CC} = 5V, T_{amb} = +25°C.
 Duration of short circuit should not exceed 1 second.
- 5. Measured with all inputs grounded and all outputs open.

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8K-bit TTL bipolar PROM (2048 \times 4)

82S185A

AC ELECTRICAL CHARACTERISTICS

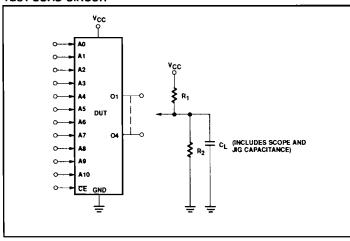
 $R_1 = 270\Omega$, $R_2 = 600\Omega$, $C_1 = 30pF$, $0^{\circ}C \le T_{amb} \le +75^{\circ}C$, $4.75V \le V_{CC} \le 5.25V$

		то		LIMITS			ļ
SYMBOL	PARAMETER		FROM	Min	Typ ¹	Max	UNIT
Access tim	ne ²						
t _{AA}		Output	Address		40	50	ns
t _{CE}		Output	Chip Enable		20	30	ns
Disable tin	ne ³						
tco		Output	Chip Disable		20	30	ns

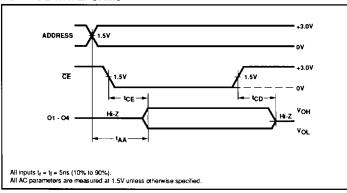
NOTES:

- 1. Typical values are at V_{CC} = 5V, T_{amb} = +25°C. 2. Tested at an address cycle time of 1 μ s. 3. Measured at a delta of 0.5V from Logic Level with R₁ = 750 Ω , R₂ = 750 Ω , C_L = 5pF.

TEST LOAD CIRCUIT



VOLTAGE WAVEFORMS



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